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Kind regards,

Team Nexperia



PMEG100V060ELPD

100 V, 6 A low leakage current Schottky barrier rectifier

20 May 2016

Product data sheet

1. General description

Maximum Efficiency General Application (MEGA) Schottky barrier rectifier, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 6$ A
- Reverse voltage: $V_R \leq 100$ V
- Low leakage current due to high Schottky barrier technology
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- High temperature $T_j \leq 175$ °C
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- Automotive LED lighting
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

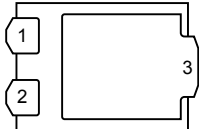
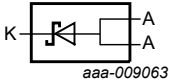
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{amb} \leq 155$ °C; square wave	-	-	6	A
V_R	reverse voltage	$T_j = 25$ °C	-	-	100	V
V_F	forward voltage	$I_F = 6$ A; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_j = 25$ °C	-	770	840	mV
I_R	reverse current	$V_R = 100$ V; $t_p \leq 3$ ms; $\delta \leq 0.03$; $T_j = 25$ °C	-	0.11	0.45	μ A



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 CFP15 (SOT1289)	 aaa-009063
2	A	anode		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG100V060ELPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG100V060ELPD	100V L06E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	100	V
I_F	forward current	$T_{sp} \leq 150\text{ }^{\circ}\text{C}$; $\delta = 1$		-	8.4	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{amb} \leq 155\text{ }^{\circ}\text{C}$; square wave		-	6	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; square wave		-	130	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
T_j	junction temperature			-	175	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	175	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	175	$^{\circ}\text{C}$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3 , standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	90	K/W
			[1][3]	-	-	70	K/W
			[1][4]	-	-	40	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	3	K/W

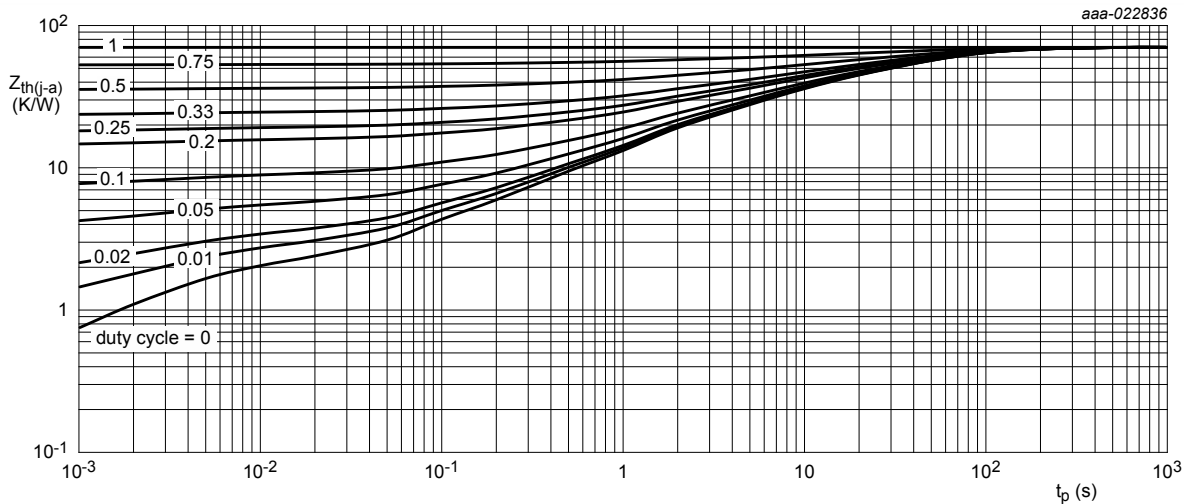
[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

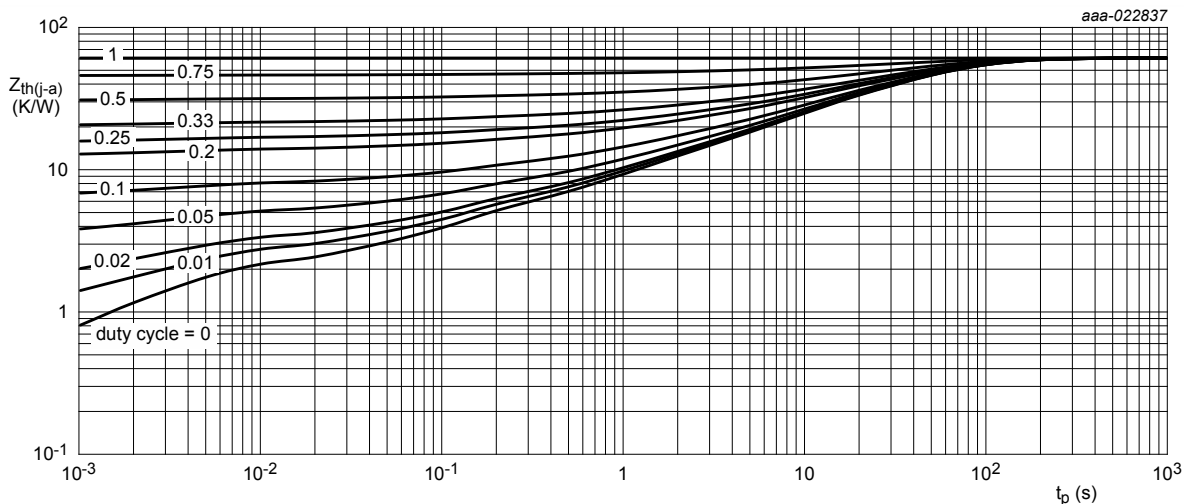
[4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[5] Soldering point of cathode tab.



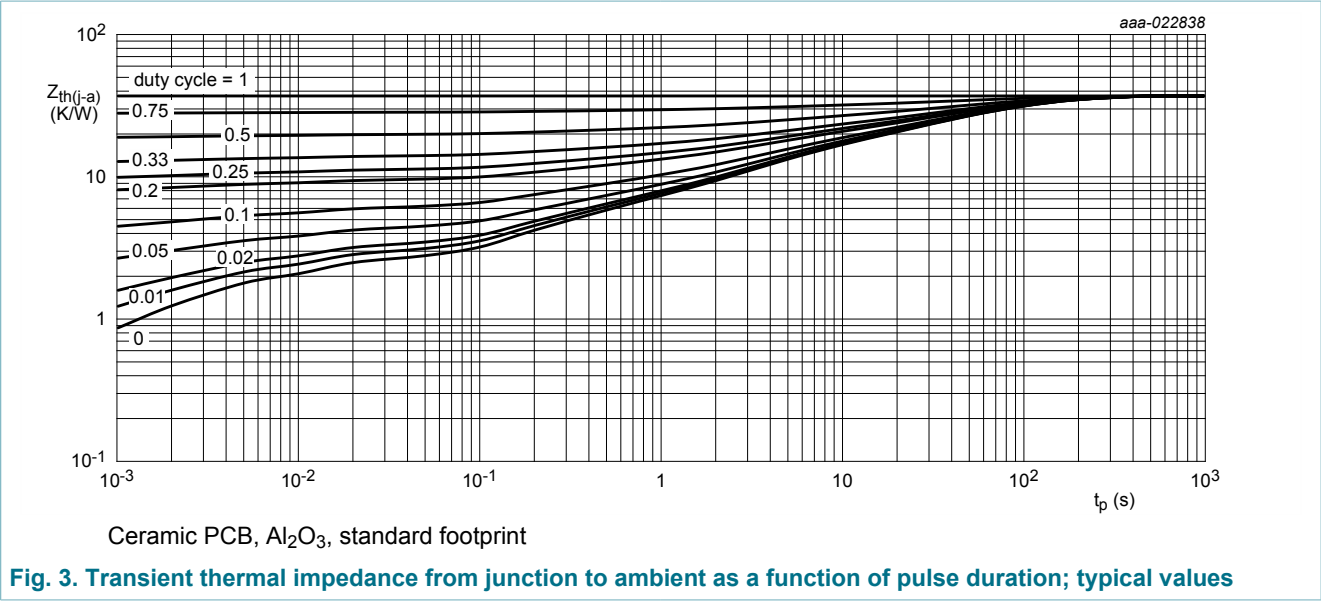
FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

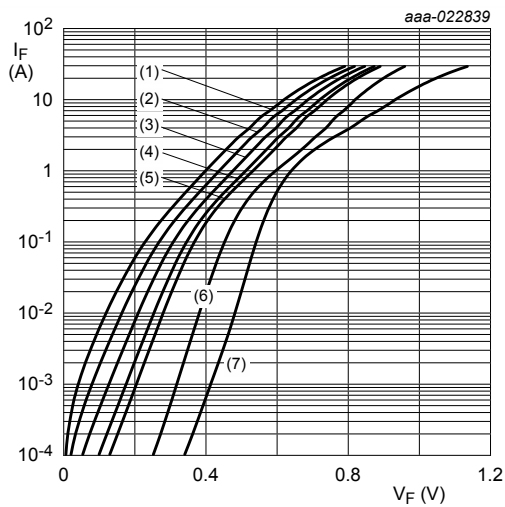
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



10. Characteristics

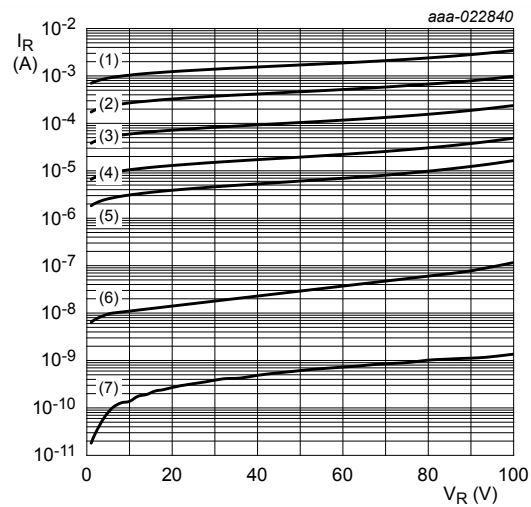
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 1 \text{ mA}$; $t_p \leq 1.2 \text{ ms}$; $\delta \leq 0.12$; $T_j = 25 \text{ }^\circ\text{C}$; pulsed	100	-	-	V
V_F	forward voltage	$I_F = 0.1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	455	-	mV
		$I_F = 1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	600	-	mV
		$I_F = 2 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	670	740	mV
		$I_F = 3 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	710	770	mV
		$I_F = 4 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	740	810	mV
		$I_F = 6 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	770	840	mV
		$I_F = 6 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = -40 \text{ }^\circ\text{C}$	-	860	970	mV
		$I_F = 6 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_j = 125 \text{ }^\circ\text{C}$	-	630	750	mV
I_R	reverse current	$V_R = 60 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.03$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.035	-	μA
		$V_R = 80 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.03$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.055	-	μA
		$V_R = 100 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.03$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.11	0.45	μA
		$V_R = 100 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.03$; $T_j = 125 \text{ }^\circ\text{C}$	-	0.22	0.8	mA
		$V_R = 60 \text{ V}$; $t_p \leq 3 \text{ ms}$; $\delta \leq 0.03$; $T_j = 150 \text{ }^\circ\text{C}$	-	0.5	2	mA
C_d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	200	-	pF
		$V_R = 4 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	120	-	pF
		$V_R = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	80	-	pF
t_{rr}	reverse recovery time	$I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(\text{meas})} = 0.1 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$	-	8	-	ns
V_{FR}	forward recovery voltage	$I_F = 0.5 \text{ A}$; $di_F/dt = 20 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ }^\circ\text{C}$	-	565	-	mV



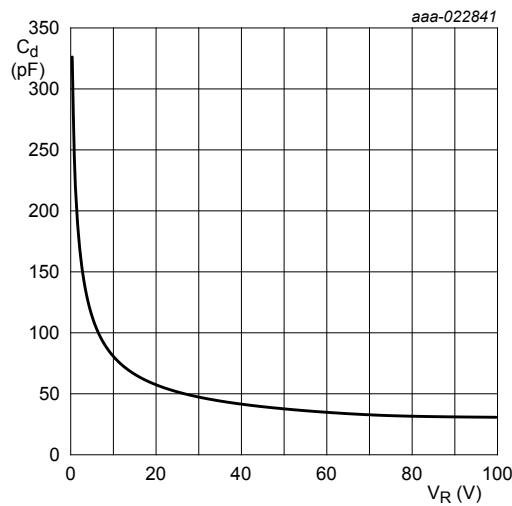
pulsed condition
(1) $T_j = 175\text{ }^{\circ}\text{C}$
(2) $T_j = 150\text{ }^{\circ}\text{C}$
(3) $T_j = 125\text{ }^{\circ}\text{C}$
(4) $T_j = 100\text{ }^{\circ}\text{C}$
(5) $T_j = 85\text{ }^{\circ}\text{C}$
(6) $T_j = 25\text{ }^{\circ}\text{C}$
(7) $T_j = -40\text{ }^{\circ}\text{C}$

Fig. 4. Forward current as a function of forward voltage; typical values

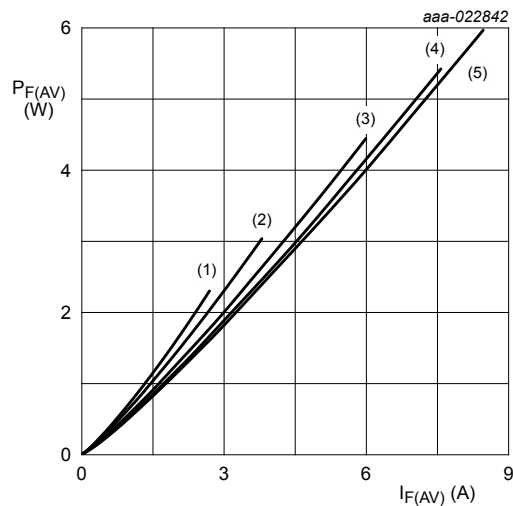


pulsed condition
(1) $T_j = 175\text{ }^{\circ}\text{C}$
(2) $T_j = 150\text{ }^{\circ}\text{C}$
(3) $T_j = 125\text{ }^{\circ}\text{C}$
(4) $T_j = 100\text{ }^{\circ}\text{C}$
(5) $T_j = 85\text{ }^{\circ}\text{C}$
(6) $T_j = 25\text{ }^{\circ}\text{C}$
(7) $T_j = -40\text{ }^{\circ}\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$
Fig. 6. Diode capacitance as a function of reverse voltage; typical values



$T_j = 100\text{ }^{\circ}\text{C}$
(1) $\delta = 0.1$
(2) $\delta = 0.2$
(3) $\delta = 0.5$
(4) $\delta = 0.8$
(5) $\delta = 1$
Fig. 7. Average forward power dissipation as a function of average forward current; typical values

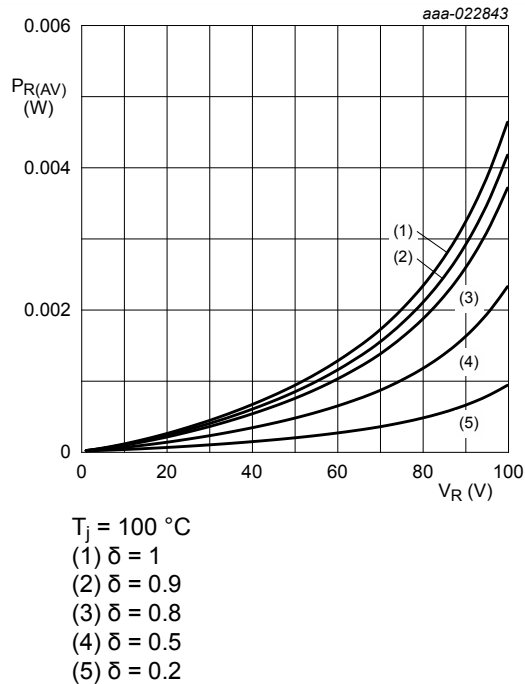


Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values

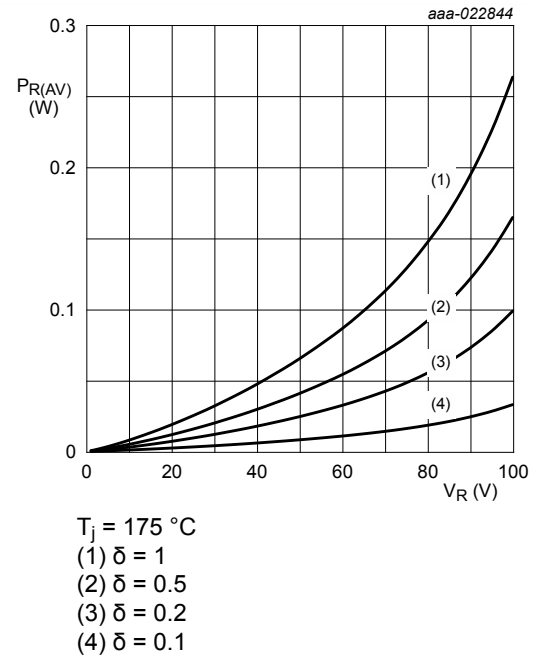


Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

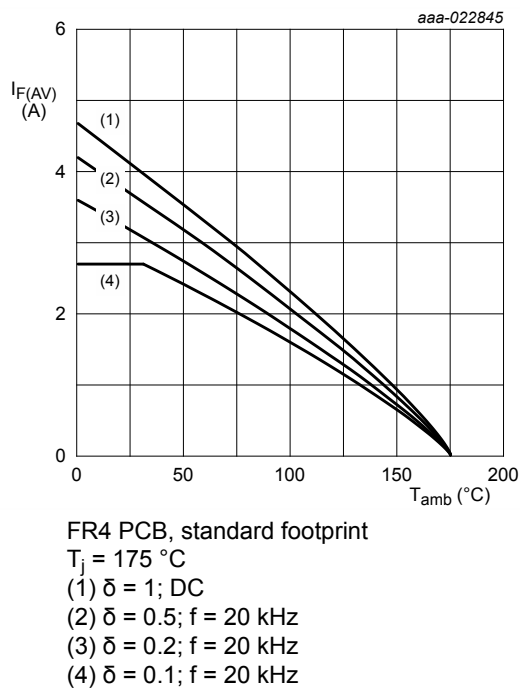


Fig. 10. Average forward current as a function of ambient temperature; typical values

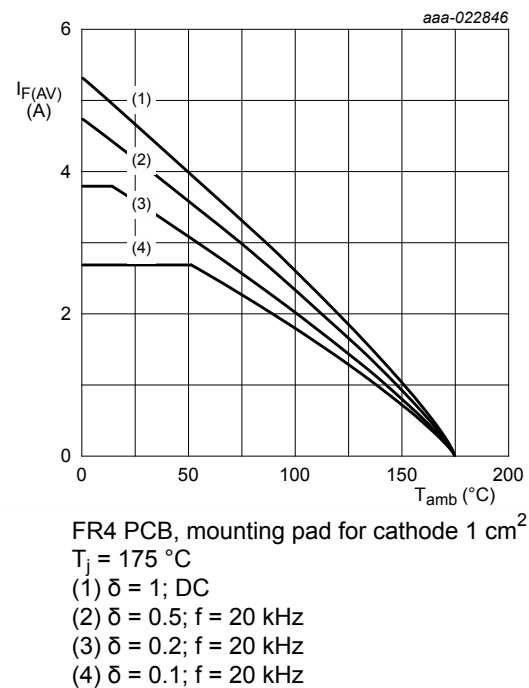
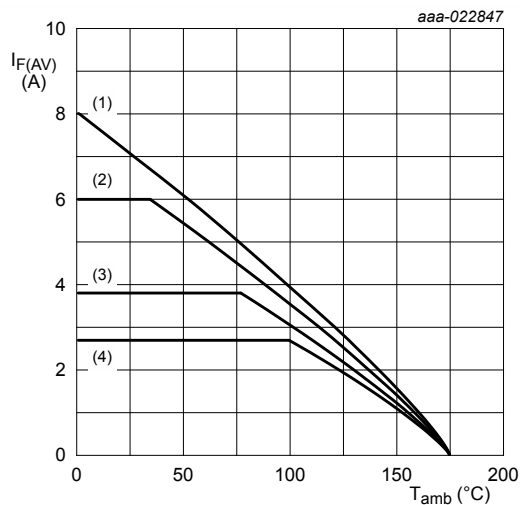
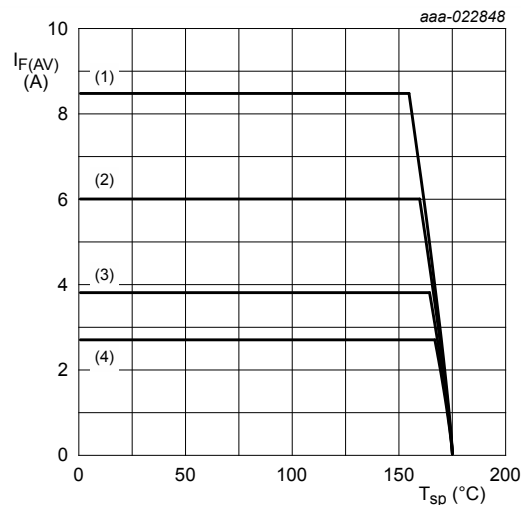


Fig. 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint
 $T_j = 175$ °C
(1) $\delta = 1$ (DC)
(2) $\delta = 0.5$; $f = 20$ kHz
(3) $\delta = 0.2$; $f = 20$ kHz
(4) $\delta = 0.1$; $f = 20$ kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



$T_j = 175$ °C
(1) $\delta = 1$ (DC)
(2) $\delta = 0.5$; $f = 20$ kHz
(3) $\delta = 0.2$; $f = 20$ kHz
(4) $\delta = 0.1$; $f = 20$ kHz

Fig. 13. Average forward current as a function of solder point temperature; typical values

11. Test information

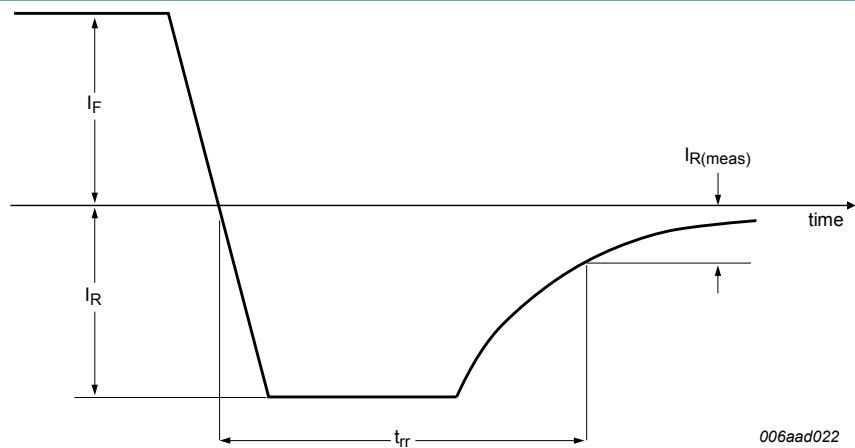


Fig. 14. Reverse recovery definition

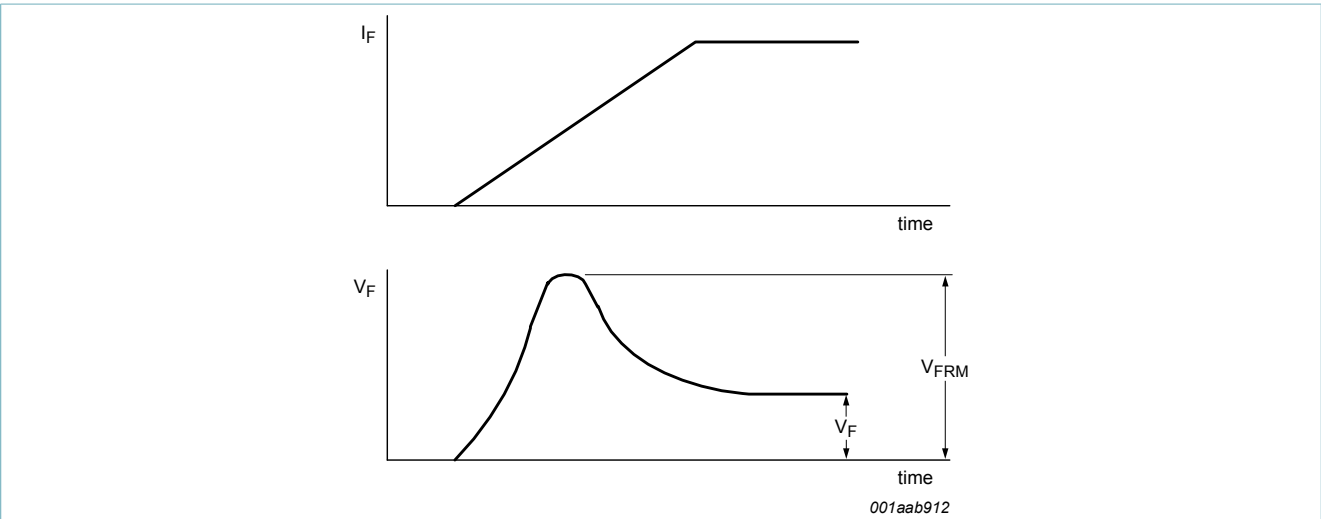


Fig. 15. Forward recovery definition

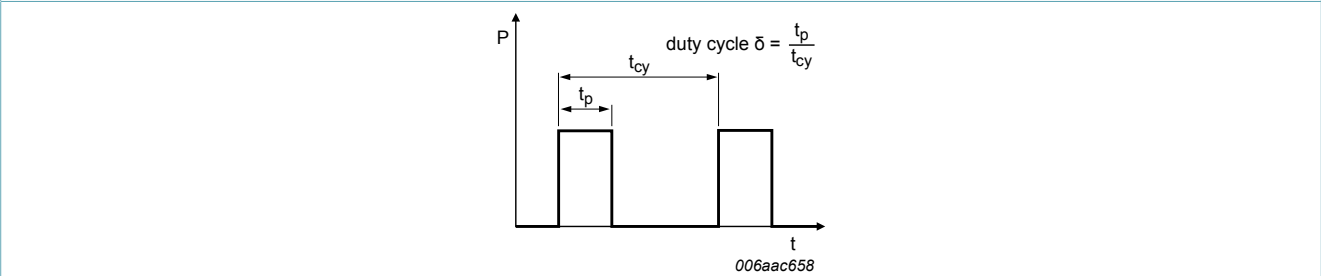


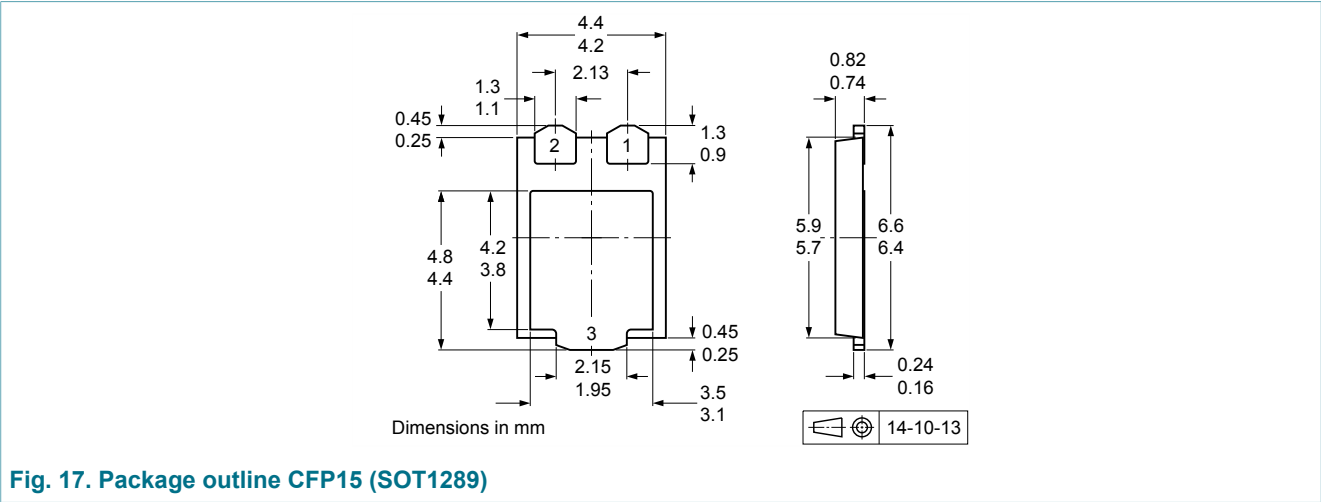
Fig. 16. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

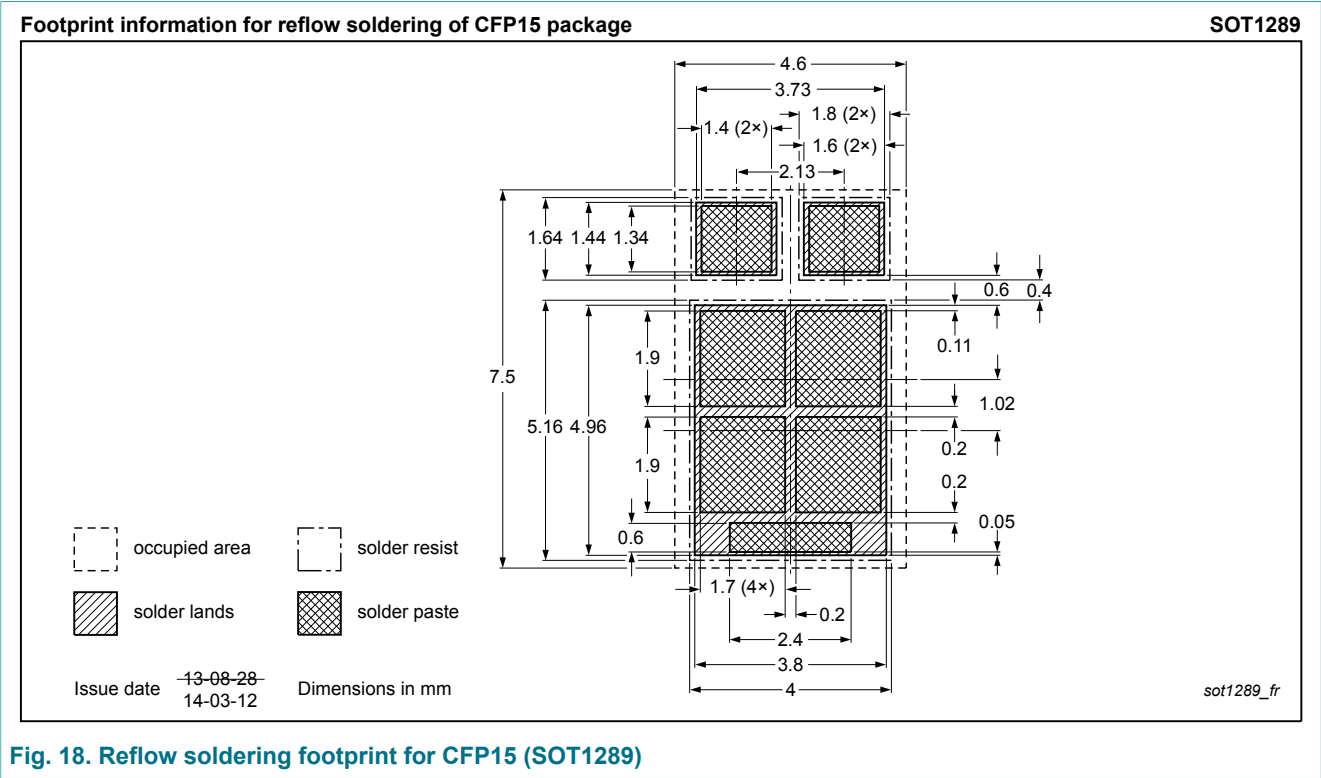
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG100V060ELPD v.1	20160520	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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